AMENDMENTS TO THE SPECIFICATION

On page 3-4, amend paragraph [0006] as follows:

[0006] There is known still another manufacturing method made up of the steps of epitaxially growing, as shown in Fig. 12A, a p-type GaAs buffer layer 311, a p-type AlGaAs current diffusion layer 312, a p-type cladding layer 313, an active layer 314, an n-type cladding layer 315, an n-type intermediate layer 316, and an n-type GaP layer 317 on an n-type GaAs substrate 310 opaque to the wavelength of emitted light, forming an n-type GaP substrate 318 thereon as shown in Fig. 12B, and then removing the n-type GaAs substrate 310 (see Japanese Patent Laid-Open Publication No. 2000-196139).